

**Amendments to the Claims**

Claims 1-40 (Cancelled).

41. (Previously presented) A transistor structure, comprising:  
a gate oxide layer on a semiconductive substrate, the gate oxide layer  
comprising silicon dioxide and having a total thickness of about 5X; the gate oxide layer  
having a nitrogen-enriched region which is only in an upper half of the gate oxide layer;  
a conductive layer on the gate oxide layer; and  
source/drain regions within the semiconductive substrate; the source/drain  
regions being gatedly connected to one another by the conductive layer.

42. (Original) The structure of claim 41 wherein the conductive layer comprises  
conductively-doped silicon.

43. (Original) The structure of claim 41 wherein the conductive layer comprises  
p-type conductively-doped silicon.

Claims 44-52 (Cancelled).